

ABSTRACT OF THE DISCLOSURE

[0060] A double-gate semiconductor device includes a substrate, an insulating layer, a fin, source and drain regions and a gate. The insulating layer is formed on the substrate and the fin is formed on the insulating layer. The source region is formed on the insulating layer adjacent a first side of the fin and the drain region is formed on the second side of the fin opposite the first side. The source and drain regions have a greater thickness than the fin in the channel region of the semiconductor device.